General Purpose Transistor

PNP Silicon

Features

• These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	-40	Vdc
Emitter-Base Voltage	V _{EBO}	-4.0	Vdc
Collector Current - Continuous	Ic	-100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

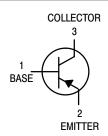
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.



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SOT-23 (TO-236) CASE 318 STYLE 6

MARKING DIAGRAM



M2C = Specific Device Code

M = Date Code*

■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBTA70LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I _C = -1.0 mAdc, I _B = 0)	V _{(BR)CEO}	-40	-	Vdc	
Emitter–Base Breakdown Voltage ($I_E = -100 \mu Adc, I_C = 0$)	V _{(BR)EBO}	-4.0	-	Vdc	
Collector Cutoff Current (V _{CB} = -30 Vdc, I _E = 0)	I _{CBO}	-	-100	nAdc	
ON CHARACTERISTICS					
DC Current Gain ($I_C = -5.0 \text{ mAdc}$, $V_{CE} = -10 \text{ Vdc}$)	h _{FE}	40	400	_	
Collector–Emitter Saturation Voltage $(I_C = -10 \text{ mAdc}, I_B = -1.0 \text{ mAdc})$	V _{CE(sat)}	-	-0.25	Vdc	
SMALL-SIGNAL CHARACTERISTICS					
Current–Gain – Bandwidth Product ($I_C = -5.0 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}, f = 100 \text{ MHz}$)	f _T	125	-	MHz	
Output Capacitanc $(V_{CB} = -10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$	C _{obo}	-	4.0	pF	

TYPICAL NOISE CHARACTERISTICS

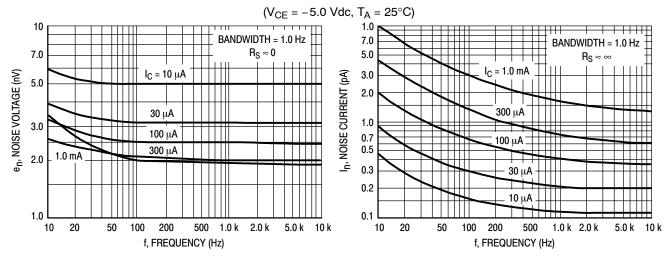


Figure 1. Noise Voltage

Figure 2. Noise Current

NOISE FIGURE CONTOURS

 $(V_{CE} = -5.0 \text{ Vdc}, T_A = 25^{\circ}\text{C})$

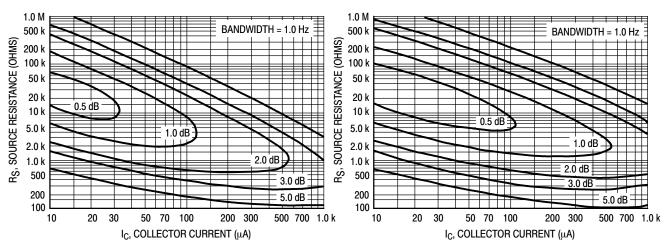


Figure 3. Narrow Band, 100 Hz

Figure 4. Narrow Band, 1.0 kHz

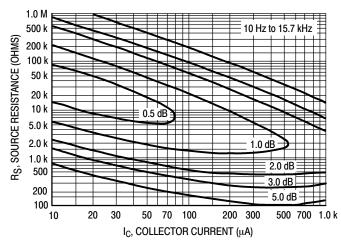


Figure 5. Wideband

Noise Figure is Defined as:

$$\text{NF} = 20 \, \text{log}_{10} \bigg[\frac{\text{e}_{\text{n}}^2 + 4 \text{KTR}_{\text{S}} + \text{I}_{\text{n}}^{-2} \text{Rs}^2}{4 \text{KTR}_{\text{S}}} \bigg]^{1/2}$$

e_n = Noise Voltage of the Transistor referred to the input. (Figure 3)

n = Noise Current of the Transistor referred to the input. (Figure 4)

 $K = Boltzman's Constant (1.38 x 10^{-23} j/{}^{\circ}K)$

T = Temperature of the Source Resistance (°K)

R_S = Source Resistance (Ohms)

TYPICAL STATIC CHARACTERISTICS

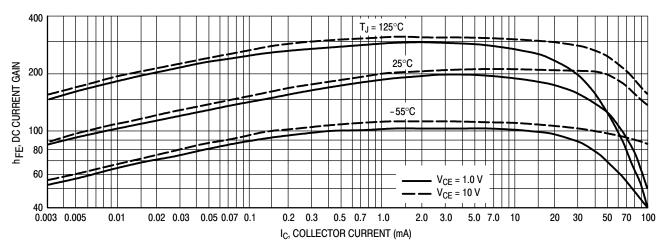


Figure 6. DC Current Gain

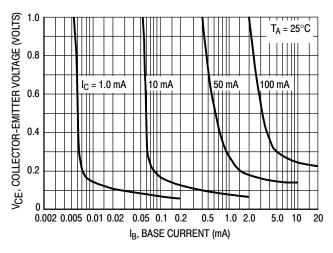


Figure 7. Collector Saturation Region

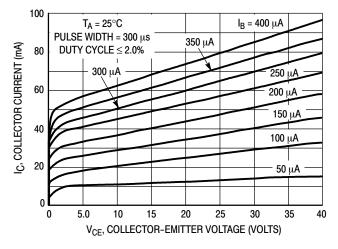


Figure 8. Collector Characteristics

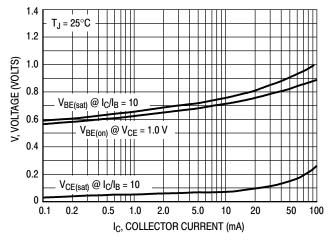


Figure 9. "On" Voltages

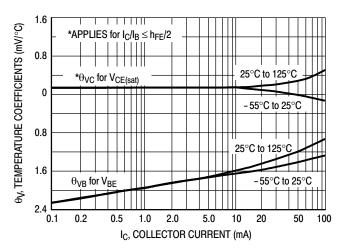
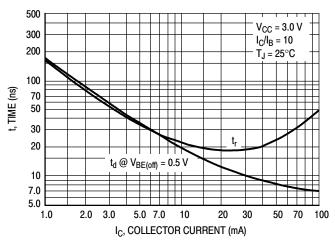


Figure 10. Temperature Coefficients

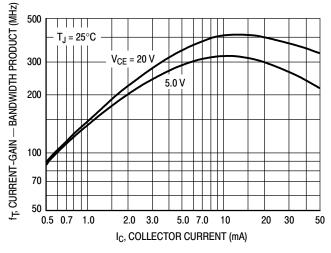
TYPICAL DYNAMIC CHARACTERISTICS



1000 $V_{CC} = -3.0 \text{ V}$ 700 $I_{\rm C}/I_{\rm B}=10$ 500 $I_{B1} = I_{B2}$ 300 $T_J = 25^{\circ}C$ 200 t, TIME (ns) 100 70 50 30 20 10 - 30 -1.0 -2.0 -3.0-5.0 -7.0 -10 -50 -70 -100 IC, COLLECTOR CURRENT (mA)

Figure 11. Turn-On Time

Figure 12. Turn-Off Time



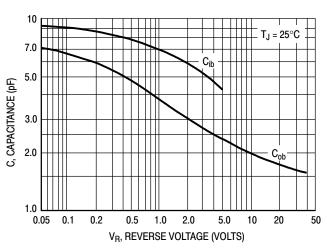
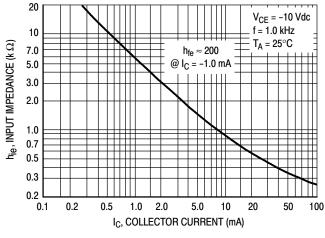


Figure 13. Current-Gain — Bandwidth Product

Figure 14. Capacitance



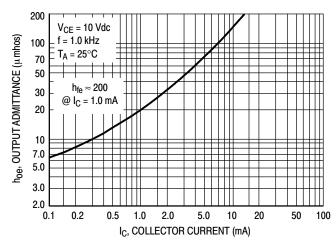


Figure 15. Input Impedance

Figure 16. Output Admittance

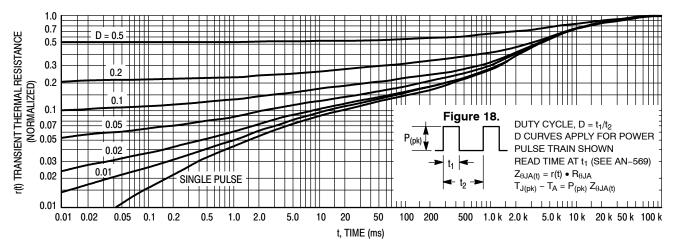


Figure 17. Thermal Response

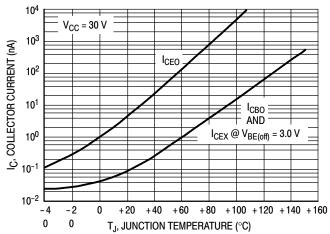


Figure 19. Typical Collector Leakage Current

DESIGN NOTE: USE OF THERMAL RESPONSE DATA

A train of periodical power pulses can be represented by the model as shown in Figure 18. Using the model and the device thermal response the normalized effective transient thermal resistance of Figure 17 was calculated for various duty cycles.

To find $Z_{\theta JA(t)}$, multiply the value obtained from Figure 17 by the steady state value $R_{\theta JA}$.

Example:

Dissipating 2.0 watts peak under the following conditions:

 $t_1 = 1.0 \text{ ms}, t_2 = 5.0 \text{ ms} (D = 0.2)$

Using Figure 17 at a pulse width of 1.0 ms and D = 0.2, the reading of r(t) is 0.22.

The peak rise in junction temperature is therefore

 $\Delta T = r(t) \times P_{(pk)} \times R_{\theta JA} = 0.22 \times 2.0 \times 200 = 88^{\circ}C.$ For more information, see AN-569.

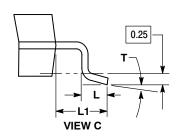


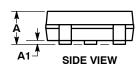
SOT-23 (TO-236) CASE 318-08 **ISSUE AS**

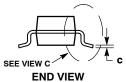
DATE 30 JAN 2018

SCALE 4:1 D Ε - 3X b

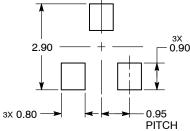
TOP VIEW







RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

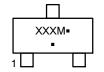
3. ANODE

NOTES:

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	O٥		10°	n۰		10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE				

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